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Low Power Integrated Receiver for ISM Band Applications

The MC13145 is a dual conversion integrated RF receiver intended for ISM band applications. It features a Low Noise Amplifier (LNA), two 50 Ω linear Mixers with linearity control, Voltage Controlled Oscillator (VCO), second LO amplifier, divide by 64/65 dual modulus Prescalar, split IF Amplifier and Limiter, RSSI output, Coilless FM/FSK Demodulator and power down control. Together with the transmit chip (MC13146) and the baseband chip (MC33410 or MC33411A/B), a complete 900 MHz cordless phone system can be implemented. This device may be used in applications up to 1.8 GHz.

- Low (<1.8 dB @ 900 MHz) Noise Figure LNA with 14 dB Gain
- Externally Programmable Mixer linearity: IIP3 = 10(nom.) to 17 dBm (Mixer1); IIP3 = 10 (nom.) to 17 dBm (Mixer2)
- 50 Ω Mixer Input Impedance and Open Collector Output (Mixer 1 and Mixer 2); 50 Ω Second LO (LO2) Input Impedance
- Low Power 64/65 Dual Modulus Prescalar (MC12053 type)
- Split IF for Improved Filtering and Extended RSSI Range
- Internal 330 Ω Terminations for 10.7 MHz Filters
- Linear Coilless FM/FSK Demodulator with Externally Programmable Bandwidth, Center Frequency and Audio level
- 2.7 to 6.5 V Operation, Low Current Drain (<27 mA, Typ @ 3.6 V) with Power Down Mode (<10 μA, Typ)
- 2.4 GHz RF, 1.0 GHz IF1 and 50 MHz IF2 Bandwidth

MC13145

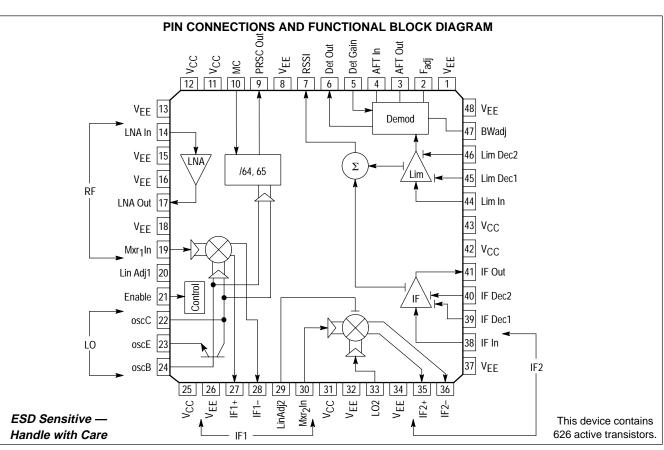
UHF WIDEBAND
RECEIVER SUBSYSTEM
(LNA, Mixer, VCO, Prescalar,
IF Subsystem,
Coilless Detector)



FTA SUFFIX PLASTIC PACKAGE CASE 932 (LQFP–48)

ORDERING INFORMATION

Device	Temperature Range	Package
MC13145FTA	$T_A = -20 \text{ to } 70^{\circ}\text{C}$	LQFP-48



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OVERALL RECEIVER SPECIFICATIONS

MAXIMUM RATINGS

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Power Supply Voltage	V _{CC} (max)	7.0	Vdc
Junction Temperature	T _J (max)	150	°C
Storage Temperature Range	T _{stg}	-65 to 150	°C
Maximum Input Signal	Pin	5.0	dBm

NOTES: 1. Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the limits in the Recommended Operating
Conditions, Electrical Characteristics tables or Pin Descriptions section.

2. Meets Human Body Model (HBM) ≤250 V and Machine Model (MM) ≤25 V. ESD data available upon request.

RECOMMENDED OPERATING CONDITIONS

L	Rating	Symbol	Min	Тур	Max	Unit
	Power Supply Voltage (T _A = 25°C)		2.7	-	6.5	Vdc
١L		VEE	0	0	0	
	Input Frequency (LNA In, Mxr ₁ In)	f _{in}	100	_	1800	MHz
	Ambient Temperature Range	T _A	-20	_	70	°C
1	Input Signal Level (with minor performance degradation)	P _{in}	_	-10	_	dBm

RECEIVER DC ELECTRICAL CHARACTERISTICS (T_A = 25°C; V_{CC} = 3.6 Vdc; No Input Signal, unless otherwise netted)

unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
Total Supply Current (Enable = V _{CC})	I _{total}	24	27	34	mA
Power Down Current (Enable = VEE)	I _{total}	_	10	50	μΑ

RECEIVER AC ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$; $V_{CC} = 3.6$ Vdc; RF In = 1.0 GHz; 1st LO Freq = 1070.7 MHz; 2nd LO Freq = 60 MHz; $f_{mod} = 1.0$ kHz; $f_{dev} = \pm 40$ kHz; IF filter bandwidth = 280 kHz, unless otherwise noted. See Figure 1 Test Circuit)

Characteristics	Input Pin	Measure Pin	Symbol	MIn	Тур	Max	Unit
SINAD @ -110 dBm LNA Input	LNA In	Det Out	SINAD	12	20	_	dB
12 dB SINAD Sensitivity (Apps Circuit with C–message filter at DetOut)	LNA In	Det Out	SINAD _{12dB}	_	-115	_	dBm
30 dB SINAD Sensitivity (No IF filter distortion within ±40 kHz)	LNA In	Det Out	SINAD _{30dB}	_	-100	_	dBm
SINAD Variation with IF Offset of ±40 kHz (No IF filter distortion within ±40 kHz)	LNA In	Det Out	-	_	5.0	_	dB
Noise Figure: LNA, 1st Mixer & 2nd Mixer	LNA In	IF Out	NF	_	3.5	5.0	dB
Power Gain: LNA, 1st Mixer & 2nd Mixer	LNA In	IF Out	G	15	19	25	dB
RSSI Dynamic Range	IF In	RSSI	-	-	80	_	dB
RSSI Current -10 dBm @ IF Input -20 dBm @ IF Input -30 dBm @ IF Input -40 dBm @ IF Input -50 dBm @ IF Input -60 dBm @ IF Input -70 dBm @ IF Input -80 dBm @ IF Input -80 dBm @ IF Input -90 dBm @ IF Input	IF In	RSSI	-	35 - - 15 - -	40 35 30 25 20 15 10 5.0	55 - - 37 - - 7.0	μΑ
Input 1.0 dB Compression Point(Measured at IF output)			P _{in1dB}	-	-18	-	dBm



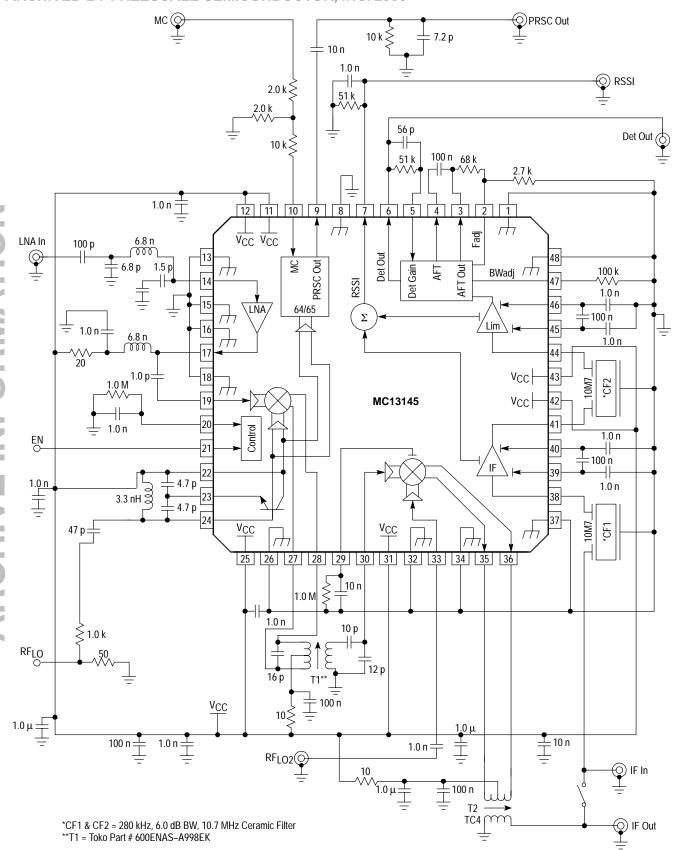
RECEIVER AC ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$; $V_{CC} = 3.6$ Vdc; RF In = 1.0 GHz; 1st LO Freq = 1070.7 MHz; 2nd LO Freq = 60 MHz; $t_{fmod} = 1.0$ kHz; $t_{fdev} = \pm 40$ kHz; IF filter bandwidth = 280 kHz, unless otherwise noted. See Figure 1 Test Circuit)

ARCHIVED BY FREESCALE SEMICONI Characteristics	UlapuOR Pin	, Measure 0 Pin	5 Symbol	MIn	Тур	Max	Unit
Input 3rd Order Intercept Point (Measured at IF output)			IIP3	-	-8.0	-	dBm
Demodulator Output Swing (50 k 56 pF Load)	IF In	Det Out	V _{out}	0.8	1.0	1.2	V _{pp}
Demodulator Bandwidth (±1.0 dB bandwidth)		Det Out	BW	-	100	-	kHz
Prescalar Output Level (10 kΩ//8.0 pF load) Prescaler 64 Frequency = 16.72968 MHz Prescaler 65 Frequency = 16.4723 MHz		PRSCout	V _{out}	0.4 0.4	0.51 0.51	0.6 0.6	V _{pp}
MC Current Input (High)		MC	l _{ih}	70	100	130	μΑ
MC Current Input (Low)		MC	lil	-130	-100	-70	μΑ
Input high voltage		Enable	V _{ih}	V _{CC} - 0.4	-	Vcc	V
Input low voltage		Enable	V _{il}	0	-	0.4	V
Input Current		Enable	l _{in}	-50	-	50	μΑ
PLL Setup Time [Note 1]	MC	PRSCout	T _{PLL}	-	10	-	nS
SNR @ -30 dBm Signal Input (<40 kHz deviation;with C-Message Filter)				_	50	_	dB
Total Harmonic Distortion (<40 kHz deviation;with C–Message Filter)				-	1.0	-	%
Spurious Response SINAD (RF In: -50 dBm)				_	12	_	dB



Figure 1. Test Circuit

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CIRCUIT DESCRIPTION

General

FM receiver incorporating a split IF. This device is designated for use as the receiver in analog and digital FM systems such as 900 Mhz ISM Band Cordless phones and wideband data links with data rates up to 150kbps. It contains a 1st and 2nd mixer, 1st and 2nd local oscillator, Received Signal Strength Indicator (RSSI), IF amplifier, limiting IF, a unique coilless quadrature detector, and a device enable function.

Current Regulation/Enable

The MC13145 is designed for battery powered portable applications. Supply current is typically 27 mA at 3.6 Vdc.

Temperature compensating, voltage independent current regulators are controlled by the Enable Pin where "high" powers up and "low" powers down the entire circuit.

Low Noise Amplifier (LNA)

The LNA is a cascoded common emitter amplifier configuration. Under very large RF input signals, the DC base current of the common emitter and cascode transistors can become very significant. To maintain linear operation of the LNA, adequate dc current source is needed to establish the 2Vbe reference at the base of the RF cascoded transistor and to provide the base voltage on the common emitter transistor. A sensing circuit, together with a current mirror guarantees that there is always sufficient dc base current available for the cascode transistor under all power levels.

1st and 2nd Mixer

Each mixer is a double-balanced class AB four quadrant multiplier which may be externally biased for high mixer dynamic range. Mixer input third order intercept point of up to 17 dBm is achieved with only 7.0 mA of additional supply current. The 1st mixer has a single–ended input at 50 Ω and operates at 1.0 GHz with -3.0 dB of power gain at approximately 100 mVrms LO drive level. The mixers have open collector differential outputs to provide excellent mixer dynamic range and linearity.

1st Local Oscillator

The 1st LO has an on-chip transistor which operates with coaxial transmssion line and LC resonant elements up to 1.8 GHz. A VCO output is available for multi-frequency operation under PLL synthesizer control.

RSSI

The received signal strength indicator (RSSI) output is a current proportional to the log of the received signal amplitude. The RSSI current output (Pin 7) is derived by summing the currents from the IF and limiting amplifier stages. An increase in RSSI dynamic range, particularly at higher input signal levels is achieved. The RSSI circuit is designed to provide typically 80 dB of dynamic range with temperature compensation.

Linearity of the RSSI is optimized by using external ceramic bandpass filters which have an insertion loss of 4.0 dB and 330 Ω source and load impedance.

IF Amplifier

The first IF amplifier section is composed of three differential stages with the second and third stages

contributing to the RSSI. This section has internal DC ARTHE MC13145 is a low power dual conversion Wideband, IN feedback and external input decoupling for improved symmetry and stability. The total gain of the IF amplifier block is approximately 40 dB up to 40MHz.

> The fixed internal input impedance is 330 Ω . When using ceramic filters requiring source and load impedances of 330 Ω , no external matching is necessary. Overall RSSI linearity is dependent on having total midband attenuation of 10 dB (4.0 dB insertion loss plus 6.0 dB impedance matching loss) for the filter. The output of the IF amplifier is buffered and the impedance is 330 Ω .

Limiter

The limiter section is similar to the IF amplifier section except that five stages are used with the middle three contributing to the RSSI. The fixed internal input impedance is 330 Ω . The total gain of the limiting amplifier section is approximately 84 dB. This IF limiting amplifier section internally drives the coilless quadrature detector section.

Coilless Quadrature Detector

The coilless detector is a unique design which eliminates the conventional tunable quadrature coil in FM receiver systems. The frequency detector implements a phase locked loop with a fully integrated on chip relaxation oscillator which is current controlled and externally adjusted, a bandwidth adjust, and an automatic frequency tuning circuit. The loop filter is external to the chip allowing the user to set the loop dynamics. Two outputs are used: one to deliver the audio signal (detector output) and the other to filter and tune the detector (AFT).

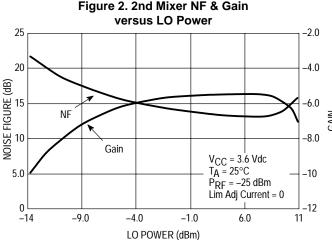


Figure 2. 2nd Mixer NF & Gain

Evaluation PCB

The evaluation PCB is a versatile board which allows the MC13145 to be configured as a dual-conversion receiver, or to characterize individual operating parameters.

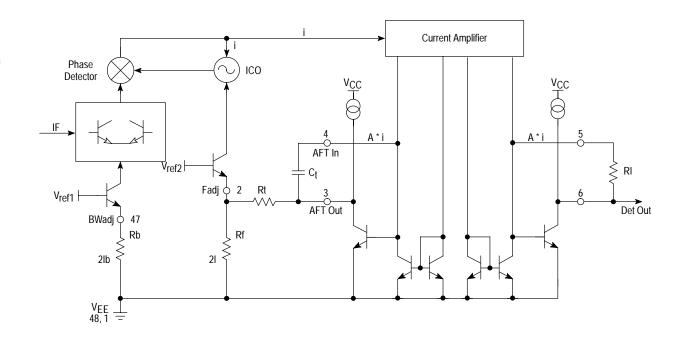
The general purpose schematic and associated parts list for a typical application are given in Figure 15. Please refer to AN1687/D and AN1691/D for additional details and applications for the device.



PIN FUNCTION DESCRIPTION

Pin	Symbol/Type	Description	Description
ARCHIVI	ED BY FREES	CALE SEMICONDUCTOR, INC. 2005 See Figure 3.	COILLESS DETECTOR Bandwidth Adjust The deviation bandwidth of the detector response is determined by the combination of an on-chip capacitor and an external resistor to ground.
2	F _{adj}		Frequency Adjust The free running frequency of the detector oscillator is defined by the combination of an on–chip capacitor and an external resistor, Radj from frequency adjust pin to ground.
1, 48	VEE		VEE, Negative Supply These pins are VEE supply for the coilless detector circuit.
3	AFT Out		AFT Out The AFT is low pass filtered with a corner frequency below the audio bandwidth allowing the error to be added to the center frequency adjust signal at Fadj, Pin 2. The low frequency high pass corner is set by the external capacitor, Ct from AFT out (Pin 3) to AFT in (Pin 4) and external resistor, Rt from AFT out to Fadj (Pin 2).
4	AFT In		AFT In The AFT in is used to set the buffer transfer function.
5	Det Gain		Detector Gain The AFT buffer is used to set the buffer transfer function.
6	Det Out		Detector Output Set gain and output level of detector with resistor to Det Out Pin.

Figure 3. Coilless Detector Internal Circuit





			Freescale Se្ពាក្រស្ ាល	ctor, Inc.
	Pin	Symbol/Type	Description	Description
	8 ARCHIV	V _{EE} ED BY FREES	CALE SEMICONDUCTOR, INC. 2005	V _{EE} , Negative Supply Voltage
	9	PRSCout	PRSC Out 1.0 mA	Prescaler Output The prescaler output provides typically 500 mVpp drive to the fin pin of a PLL synthesizer. Conjugately matching the interface will increase the drive delivered to the PLL input.
	10	MC	VEE DE D	Dual Modulus Control Current Input This requires a current input of typically 200 μApp.
	11, 12	Vcc	17	V _{CC} , Positive Supply V _{CC} pin is taken to the incoming positive battery or regulated dc voltage through a low impedance trace on the PCB. It decoupled to V _{EE} ground at the pin of the IC.
	14	LNA In	LNA _{out} 15, 16 VEE VEE	LNA In The input is the base of the common emitter transistor. Minimum external matching is required to optimize the input return loss and gain.
	13, 15, & 16	VEE	V _{EE} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref1} V _{ref1} V _{ref1} V _{ref1} V _{ref1} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref1} V _{ref1} V _{ref1} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref1} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref1} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref2} V _{ref2} V _{ref1} V _{ref2} V _{ref}	VEE, Negative Supply VEE pin is taken to an ample dc ground plane through a low impedance path. The path should be kept as short as possible. A minimum two sided PCB is recommended so that ground returns can be easily made through via holes.
	17	LNAout		LNA Out The output is from the collector of the cascode transistor amplifier. The output may be conjugately matched with a shunt L (needed to dc bias the open collector), and series L and C network.
	19	Mxr ₁ In	LinAdj1	1st Mixer Input The mixer input impedance is broadband 50 Ω for applications up to 2.4 GHz. It easily interfaces with a RF ceramic filter.
	20	Lin Adj1	Mxr ₁ In	1st Mixer Linearity Control The mixer linearity control circuit accepts approximately 0 to 300 μA control current to set the dynamic range of the mixer. An Input Third Order Intercept Point, IIP3 of 17 dBm may be achieved at 300 μA of control current.



Pin	Symbol/Type	Description	Description
21 ARCHIVI	Enable	CALE SEMICONDUCTOR, INC. 2005	Enable Enable the receiver by pulling the pin up to V _{CC} .
26	VEE	 27	V _{EE} , Negative Supply V _{EE} supply for the mixer IF output.
27	IF1+	V _{EE}	1st Mixer Outputs The Mixer is a differential open collector output configuration which is designed to use over a wide frequency range. The differential output of the mixe has back to back diodes across them to limit the output voltage swing and to prevent pulling of the
28	IF1–	28 IF1-	VCO. Differential to single—ended circuit configuration and matching options are shown in the Test Circuit. Additional mixer gain can be achieved by matching the outputs for the desired passband Q.
22	Collector	25	On–board VCO Transistor The transistor has the emitter, base, collector, VCC and VEE pins available. Internal biasing which is
23	Emitter	Vcc 24	compensated for stability over temperature is provided. It is recommended that the base pin is pulled up to VCC through an RFC chosen for the particular oscillator center frequency.
24	Base	Base	particular contact requests,
25	VCC	V _{EE} = 23	VCC, Positive Supply Voltage A VCC pin is provided for the VCO. The operating supply voltage range is from 2.7 Vdc to 6.5 Vdc.
18, 26	VEE	22	V _{EE} , Negative Supply Voltage
29	Lin Adj2	29 Lin Adj2	2nd Mixer Linearity Control The mixer linearity control circuit accepts approximately 0 to 400 μA control current to set the dynamic range of the mixer. An Input Third Order Intercept Point, IIP3 of 17 dBm may be achieved at 400 μA of control current. IIP3 default with no external bias is 10 dBm.
30	Mxr2 In	30	2nd Mixer Input The mixer input impedance is broadband 50 Ω .
31	VCC	\$ ↓450 μA	V _{CC} , Positive Supply



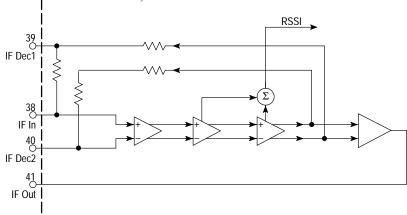
Pin	Symbol/Type	Description	Description
32, 34	VFF	CALE SEMICONDUCTOR, INC. 2005	V _{EE} , Negative Supply Voltage
33	LO2	LO Out- (to Mxr2)	2nd Local Oscillator The 2nd LO input impedance is broadband 50 Ω ; it is driven from an external 50 Ω source. Typical leve is –15 to –10 dBm.
35	IF2+	VEE = 35	2nd Mixer Outputs The Mixer is a differential open collector configuration.
36	IF2-	34 VEE = 36 IF2-	
37	VEE	See Figure 4.	V _{EE} , Negative Supply Voltage
38	IF In		IF Amplifier Input IF amplifier input source impedance is 330 Ω . The three stage amplifier has 40 dB of gain with 3.0 dB bandwidth of 40 MHz.
39, 40	IF Dec1, IF Dec2		IF Decoupling These pins are decoupled to V _{CC} to provide stable operation of the limiting IF amplifier.
41	IF Out		IF Amplifier Output IF amplifier output load impedance is 330 Ω .
42	Vcc		V _{CC} , Positive Supply Voltage
7	RSSI		RSSI The RSSI circuitry in the 2nd & 3rd amplifier stages outputs a current when the output of the previous stage enters limiting. The net result is a RSSI current which represents the logarithm of the IF input voltage. An external resistor to ground is used

to provide a voltage output.



Figure 4. IF Amplifier Functional Diagram

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Pin	Symbol/Type	Description	Description
43	Vcc	See Figure 5.	V _{CC} , Positive Supply Voltage
44	Lim In		Limiting Amplifier Input Limiting amplifier input source impedance is 330 Ω . This amplifier has 84 dB of gain with 3.0 dB bandwidth of 40 MHz; this enables the IF and limiting ampliers chain to hard limit on noise.
45, 46	Lim Dec1, Lim Dec2		If Decoupling These pins are decoupled to V _{CC} to provide stable operation of the 2nd IF limiting amplifier.
7	RSSI		RSSI The RSSI circuitry in the 2nd, 3rd, & 4th amplifier stages outputs a current when the output of the previous stage enters limiting. The net result is a RSSI current which represents the logarithm of the IF input voltage. An external resistor to ground is used to provide a voltage output.

Figure 5. Limiter Amplifier Functional Diagram

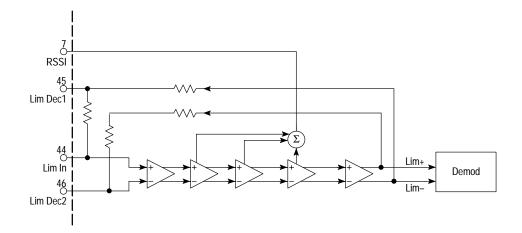




Figure 6. 2nd Mixer Gain ARCHIVED BY FREESCALE SEMICONDUCTOR, INC. 2005 $V_{CC} = 3.6 \text{ V}$ $T_A = 25^{\circ}\text{C}$ -6.4 $P_{RF} = -25 \text{ dBm}$ Lin Adj Current = 400 μA -6.8GAIN (dB) -7.2 -7.6-8.0 -20 -18 -16 -14 -12 -10 LO DRIVE (dBm)

Versus LO Drive

5.0

4.0

4.0

2.0

1.0

VCC = 3.6 V
TA = 25°C
Lin Adj Current = 400 μA

LO DRIVE (dBm)

Figure 7. 2nd Mixer P_{1dB}

Figure 8. 2nd Mixer IP3/P1dB versus Lin Adj Current 18 16 14 IP3 12 V_{CC} = 3.6 V T_A = 25°C 10 PLO = -15 dBm8.0 Adj Channel = 75 kHz 6.0 P_{1dB} 4.0 2.0 0 100 LIN ADJ CURRENT (µA)

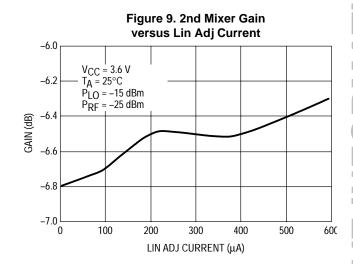
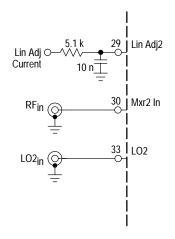
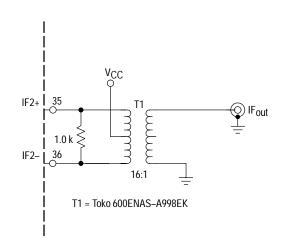


Figure 10. Test Circuit for Figures 6 thru 9.







APPLICATION INFORMATION

Input Matching / Components

mixer to provide image frequency rejection. The filter is selected based on cost, size and performance tradeoffs. Typical RF filters have 1.5 to 2.5 dB insertion loss. The evaluation PC board layout accommodates ceramic RF filters which are offered by various suppliers.

Interface matching between the LNA, RF filter and the mixer will be required. The interface matching networks shown in the evaluation circuit are designed for 50 Ω interfaces.

1st Mixer Output & 2nd Mixer Input Interface Matching

In a wideband system the primary sensitivity of the receiver backend may be achieved before the last mixer. The evaluation circuit shows the matching and impedance transformation network bewtween the 1st mixer open collector differential outputs and 2nd mixer single ended 50 ohm input. This adjustable shielded transformer and tapped capacitor transform network does two things: 1) bandpass limits the 1st IF signal with a loaded Q of approximately 40 and 2) provides adequate second image rejection and a low cost alternative to a SAW filter.

However, a SAW filter may be selected as a more costly alternative while providing improved 2nd image rejection and a fixed tuned 1st IF filter.

2nd Mixer & Limiting IF Matching / Filtering

A simple LCR network is needed to interface the 2nd mixer differential outputs to 330 ohm ceramic filters or directly to the 330 ohm IF input. TDK, Toko and Murata offer single 10.7 MHz ceramic filters with various 3.0 dB bandwidths from 110 to 380 kHz. Murata offers a series-parallel resonator pair (part number KMFC545) with a 3.0 dB bandwidth of ±325 kHz and a maximum insertion loss of 5.0 dB. However, even the series-parallel ceramic filter pair yields only a maximum bandpass of 650 kHz. In some data applications a wider band IF bandpass is necessary.

Local Oscillators - VHF/UHF Applications

The on-chip transistor may be used for HF and VHF local oscillator with higher order overtone crystals. It is recommended that a Butler overtone oscillator configuration is used. The crystal is driven from the emitter and is coupled to the high impedance base through a capacitive tap network. Operation at the desired overtone frequency is ensured by the parallel resonant circuit formed by an inductor and the tap capacitors and parasitic capacitances of the on-chip transistor and PC board. A high tolerance, high Q ceramic or air wound surface mount component may be used if the other components have tight enough tolerances; however, a variable inductor provides an adjustment for gain and frequency of the resonant tank ensuring lock up and start-up of the crystal oscillator. The overtone crystal is chosen with ESR of typically 80 ohms and 120 ohms maximum; if the resistive loss in the crystal is too high the performance of oscillator may be impacted by lower gain margins.

A series LC network to ac ground (which is V_{CC}) is comprised of the inductance of the base lead of the on-chip transistor and PC board traces and tap capacitors. Parasitic oscillations often occur in the 200 to 900 MHz range. A small resistor is placed in series with the base (pin 9) to cancel the

negative resistance associated with this undesired mode of ARTI is destrable to use a RE ceramic of SAW filter before the, IN oscillation. Since the base input impedance is so large a small resistor in the range of 27 to 68 ohms has very little effect on the desired Butler mode of oscillation.

> The crystal parallel capacitance, C_0 , provides a feedback path that is low enough in reactance at frequencies of 5th overtones or higher to cause trouble. Co has little effect near resonance because of the low impedance of the crystal motional arm (R_m-L_m-C_m). As the tunable inductor which forms the resonant tank with the tap capacitors is tuned off the crystal resonant frequency it may be difficult to tell if the oscillation is under crystal control. Frequency jumps may occur as the inductor is tuned. In order to eliminate this behavior an inductor, L_0 , is placed in parallel with the crystal. Lo is chosen to be resonant with the crystal parallel capacitance, Co, at the desired operation frequency. The inductor provides a feedback path at frequencies well below resonance; however, the parallel tank network of the tap capacitors and tunable inductor prevent oscillation at these frequencies.

Coilless Detector

The coilless detector (see Figure 3) is unique and offers cost and performance advantages over the conventional quadrature detector. It consists of a current controlled oscillator (ICO) and a phase detector. The error current, I is also amplified to provide an output, and the output is duplicated and filtered and fed back to the oscillator to provide automatic fine tuning (AFT).

The oscillator free running frequency, fo is set by Rf and is calculated by the following equation where C is approximately 4.0 pF:

$$fo = 1/(8*Rf*C)$$

The demodulator bandwidth is set by Rb and is shown in Figure 14.

The AFT is filtered by Ct and Rt. The low pass pole creates a high pass pole in the overall demodulator frequency response at:

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$$A/(2*\pi*Ct*Rt)$$

where A, the current gain = 10.

Typical coilless detector output level is:

For example, if peak deviation is 25 kHz, i = 250 μ A at fJF = 10.7 MHz, and RI is 50 k Ω ; then V_{out} is 292 mVp or 584 mVpp.

The AFT Out pin is capable of voltage swings from about 300 mV to V_{CC} – 300 mV. At these extreme values, the AFT circuit can become saturated and very long detector lock-up times may be observed. It is best, therefore, to limit the AFT Out swing from about 500 mV to V_{CC} – 500 mV and attempt to center the AFT Out voltage at V_{CC}/2 for a detector lock

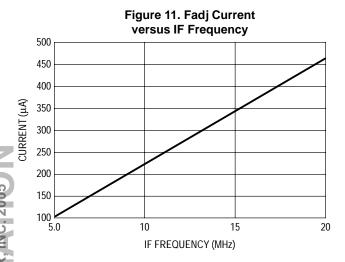
As an example, for $V_{CC} = 2.7 \text{ V}$, the ideal AFT Out voltage at lock would be 1.35 V, with an available swing of 0.5 V to 2.2 V (1.7 V total). If the AFT tuning range is to be ± 500 kHz, this corresponds to an adjustment current of 1.0 MHz/f_{IF}*i. From Figure 11, to set fif at 10.7 MHz, i is approximately 240 μA, and the total adjustment current range is therefor about 22.4 µA over a 1.7 V total swing, or Rt = 75.9 k. At lock,

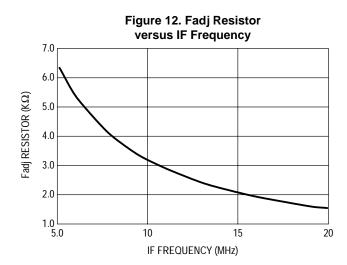


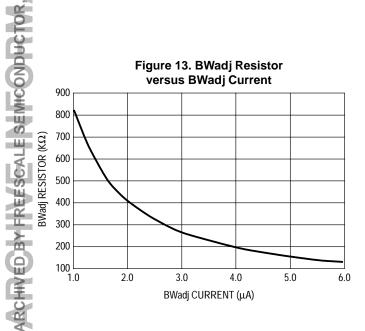
current equaling (AFT Out – Fadj)/Rt will be flowing into the Fadj node. This current then is approximately (1.35 V –

0.7 V)/75.9 k Ω or 8.6 μ A. The Fadj resistor, Rf, is therefore equal to 0.7 V/(240 μ A + 8.6 μ A) or about 2.82 k Ω .

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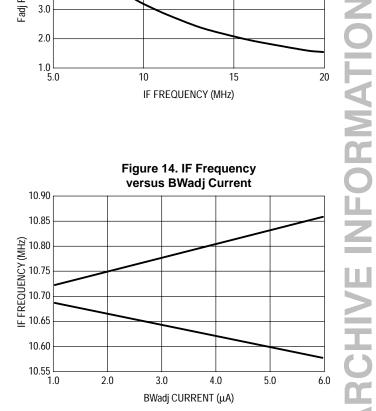




Table 1. LNA S-Parameters: 3.6 Vdc

	Freq	S11	S11	S21	S21	S12	S12 Ang	S22 mag	S22 Ang
1				MICQUEDUC.		005 Mag			
	25	0.84	-3.0	10.8	176	0.00005	-27	1.0	-1.2
	50	0.84	-7 1	10.7	171	0.0004	76	1.0	-3.7
	100	0.83	– 15	10.3	162	0.0006	61	0.99	-4.9
	150	0.81	-22	10.	154	0.0011	91	0.99	-7.3
	200	0.78	-28	9.6	147	0.001	60	0.99	-9.7
	300	0.73	-41	9.0	132	0.002	42	0.99	-15
	400	0.66	-50	7.8	116	0.00070	22	0.95	-19
	450	0.64	-54	7.4	111	0.0014	39	0.96	-21
	500	0.62	-59	7.0	106	0.0009	69	0.96	-23
	750	0.51	– 77	5.5	80	0.0013	- 51	0.94	-33
	800	0.49	-80	5.2	75	0.002	-80	0.93	-36
	850	0.47	-81	4.9	71	0.004	-120	0.92	-37
	900	0.46	-82	4.6	67	0.0057	-130	0.92	-38
	950	0.44	—82	4.3	62	0.008	-142	0.91	-40
	1000	0.45	-81	3.9	58	0.014	-162	0.95	-41
	1250	0.55	-94	3.5	47	0.029	140	0.099	-50
	1500	0.48	-120	3.1	24	0.02	63	0.94	-65
	1750	0.43	-126	2.5	6.9	0.0066	79	0.93	-74
	2000	0.43	-135	2.1	-9.9	0.0099	129	0.92	-85
	2250	0.45	-145	1.8	-27	0.017	133	0.91	-96
	2500	0.47	-155	1.5	-43	0.021	132	0.89	-106
	2750	0.51	-167	1.2	-60	0.03	130	0.88	-118
	3000	0.55	-180	1.0	-78	0.039	120	0.85	-129



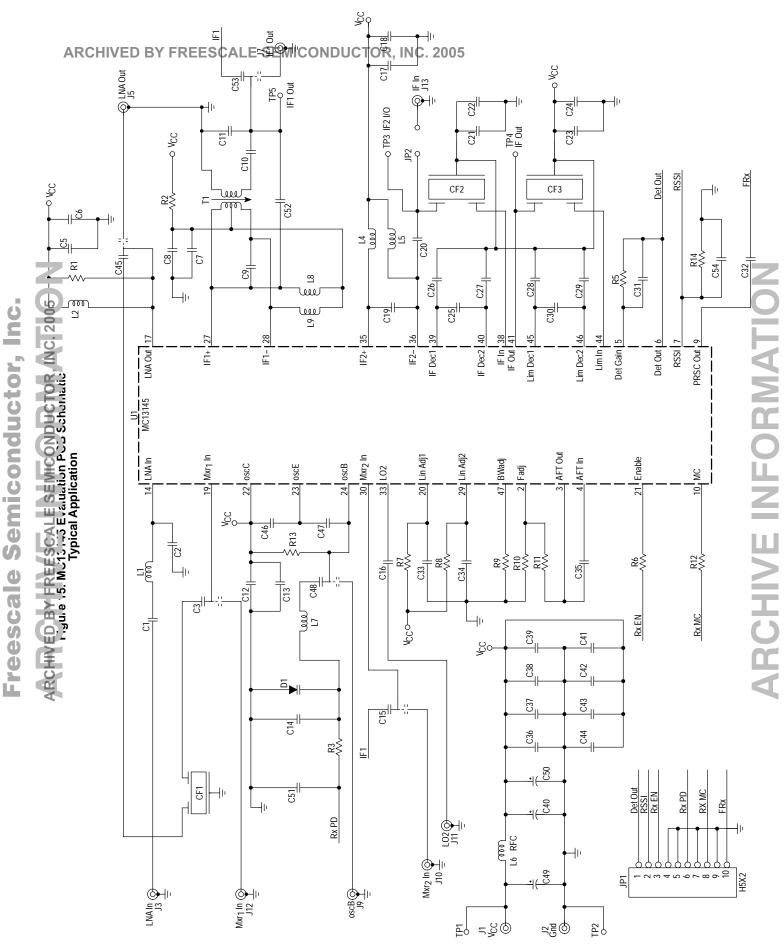
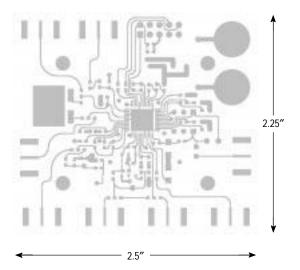


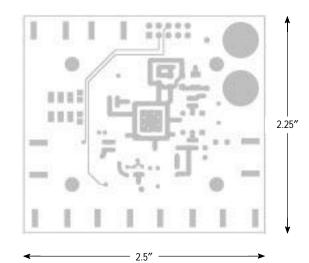


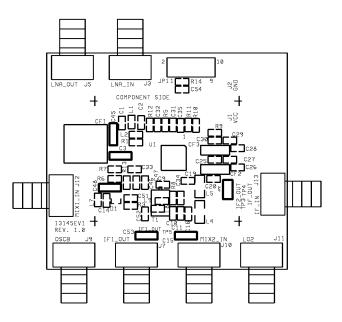
Figure 16. Evaluation PCB Component Side

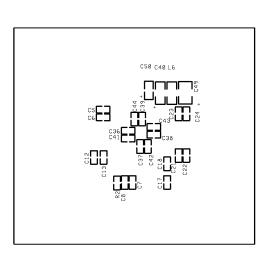
Figure 17. Evaluation PCB Solder Side

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CF1	TDK CF6	118702	C49	22
	or TDK CF6	118902	C50	1.0
CF2,CF3	Toko Type CFSK	Series	R1,R7,R8,I	L8,L9,C52,
	SK107MX-A	E-XXX	J5,J7,J9,J1	0,J12,J13 No Component
C1,C3,C5,C7,C13,C17,C31,			D1	MMBV809LT1
C41,C42,C43	,C44,C48,C51	100 p	L1	6.8 n
C2		1.5 p	L2	5.6 n
C6,C12,C21,	C23,C26,C27,	·	L4, L5	2.7 μ
C28,C29,C33	3,C34,C36,C37,		L6	RFĊ
C38,C39,C54		1.0 n	L7	2.7 n
C8,C15,C16,	C18,C32,C53	0.01	R2	10
C9		16 p	R3	33 k
C10		10 p	R5	27 k
C11		12 p	R6,R11,R1	2,R14 51 k
C14		2.0–4.0 p	R9	68 k
C19		36 p	R10	2.85 k
C20		39 p	R13	51 or RFC
C22,C24,C25	,C30,C35	0.1	T1	Toko A638AN-A099YWN
C40		10 μ	U1	MC13145FTA
C45		3.3 p		
C46,C47		2.0 p		

J3,J11 SMA EF Johnson 142–0701–851
J1,J2 Bananna Johnson Components
108–0902–001
JP1 Header, 5x2

 $\label{lem:default Units: Ohms, Microfarads, and Microhenries} Default \ Units: \ Ohms, \ Microfarads, \ and \ Microhenries$



Freescale

Freescale Samiganductor, Inc.

Figure 18. Evaluation PCB Ground Plane

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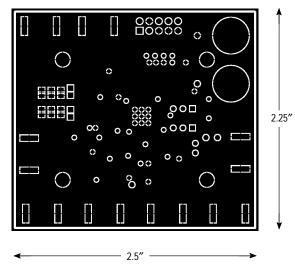
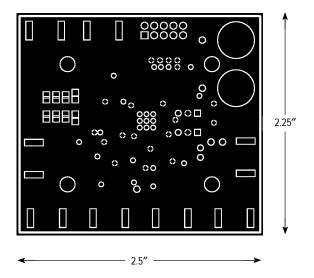
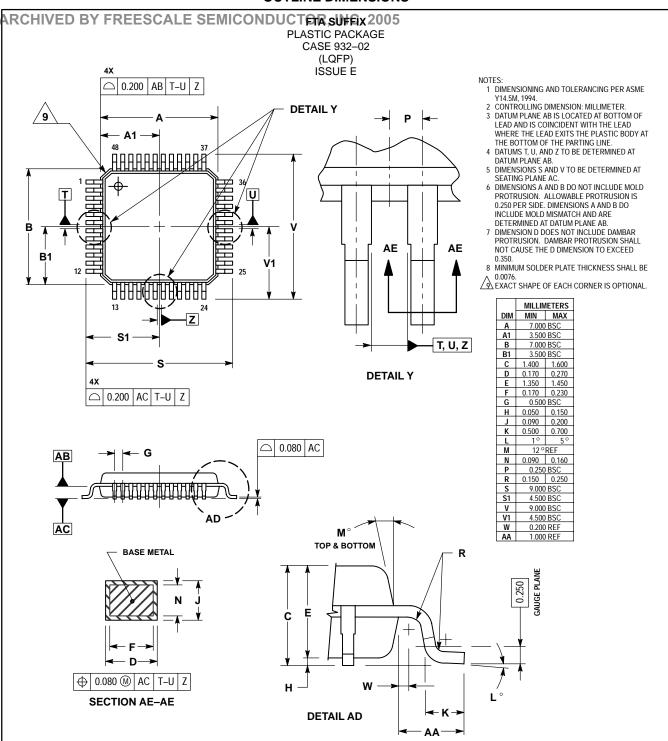


Figure 19. Evaluation PCB Power Plane





OUTLINE DIMENSIONS



NFORMATION



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